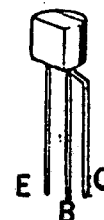


BF420 and BF421 are complementary NPN/PNP silicon planar epitaxial transistor. Designed for high voltage video amplifiers in colour television receivers including grid drive and in driver stages of high voltage line deflection circuits.

TO-92



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	300V
Collector-Emitter Voltage	VCEO	300V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	200mA
Total Power Dissipation (mounted on a copper plate of length 3mm max and area 1cm ²)	Ptot	830mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	300		V	IC=10μA IE=0
Collector-Emitter Breakdown Voltage	BVCEO	300		V	IC=2.5mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		10	nA	VCB=200V IE=0
Emitter Cutoff Current	IEBO		10	nA	VEB=5V IC=0
D.C. Current Gain	HFE	40			IC=25mA VCE=20V
Current Gain-Bandwidth Product	fT	60		MHZ	IC=10mA VCE=10V
Output Capacitance	Cob	2.0typ		pF	VCB=30V IE=0 f=1MHZ



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